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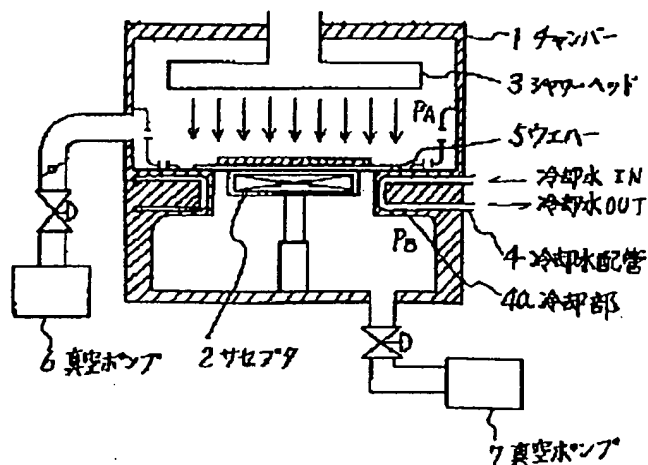
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APPLICANT : NEC CORP;

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TITLE : TUNGSTEN CVD EQUIPMENT



ABSTRACT : PURPOSE: To restrain the growth of a tungsten film on the peripheral part of a wafer where a barrier film is not formed, and prevent exfoliation of the tungsten film and generation of particles which are to be caused by imperfect adhesion to a base oxide film.

CONSTITUTION: A stage retaining a wafer 5 is divided into a susceptor 2 having a heater and a cooling part 4a surrounding the susceptor 2. A chamber 1 is divided into an upper chamber and a lower chamber by the retained wafer 5, and the respective chambers are provided with independent vacuum pumps 6, 7. By the vacuum pumps 6, 7, vacuum pressure difference is generated between above and below the wafer 5, and the wafer 5 is brought into contact closely with the susceptor and the cooling part 4a. Since the peripheral part of the wafer 5 is in contact with the cooling part 4a, a tungsten film is not formed, and film exfoliation also is not generated.

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